NSN 5961-01-051-3933

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Inclosure Material:
Metal all transistor
Overall Length:
0.170 inches all transistor and 0.210 inches all transistor
Terminal Length:
0.500 inches all transistor
Overall Diameter:
0.209 inches all transistor and 0.230 inches all transistor
End Application:
An/grc171 (v) 1
Internal Configuration:
Field effect all transistor
Channel Polarity And Control Type (non-core):
N-channel junction type all transistor
Component Function Relationship:
Matched
Component Name And Quantity:
2 transistor
Mounting Method:
Terminal all transistor
Terminal Circle Diameter:
0.100 inches all transistor
Field Force Effect Type:
Electrostatic charge
Semiconductor Material:
Silicon all transistor
Voltage Rating In Volts Per Characteristic:
30.0 breakdown voltage, gate-to-source, with all other terminals short-circuited to source all transistor
Current Rating Per Characteristic:
15.00 milliamperes zero-gate-voltage source current megawatts all transistor
Power Rating Per Characteristic:
300.0 milliwatts small-signal input power, common-collector absolute
Special Features:
T.O. 31r2-2grc171-4; n/h/a circuit card assembly
Test Data Document:
13499-352-0756 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc
excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Quantity:
4 uninsulated wire lead all transistor
Shelf Life:
N/a

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Unit Of Measure:

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Demilitarization:

No

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